

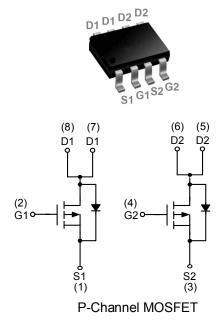
#### **Features**

- -30V/-8.9A,  $R_{DS(ON)}$ =21mΩ(max.) @  $V_{GS}$ =-10V  $R_{DS(ON)}$ =32mΩ(max.) @  $V_{GS}$ =-4.5V
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

### **Applications**

Power Management in Notebook Computer,
 Portable Equipment and Battery Powered
 Systems.

#### **SOP-8 Pin Configuration**



# **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit					
Common Ratings								
V <sub>DSS</sub>	Drain-Source Voltage	-30	V					
$V_{GSS}$	Gate-Source Voltage	±25	]					
T <sub>J</sub>	Maximum Junction Temperature	150	°C					
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	] [					
Is	Diode Continuous Forward Current	T <sub>A</sub> =25°C	-1					
	Continuous Drain Current	T <sub>A</sub> =25°C	-8.9	A				
l <sub>D</sub>		T <sub>A</sub> =70°C	-7.1					
I <sub>DM</sub> <sup>a</sup>	Pulsed Drain Current	T <sub>A</sub> =25°C	-35					
P <sub>D</sub>	Maximum Power Dissipation	T <sub>A</sub> =25°C	2.5	W				
		T <sub>A</sub> =70°C	1.6	VV				
$R_{\scriptscriptstyle{ hetaJA}}$	Thermal Resistance-Junction to Ambient	t ≤ 10s	50					
		Steady State	90	°C/W				
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	20					
I <sub>AS</sub> <sup>b</sup>	Avalanche Current, Single pulse	L=0.1mH	24	A				
		L=0.5mH	14					
E <sub>AS</sub> <sup>b</sup>	Avalancha Energy, Single nulse	L=0.1mH	29	mJ				
	Avalanche Energy, Single pulse	L=0.5mH	49					

Note a: Pulse width is limited by maximum junction temperature.

Note b : UIS tested and pulse width are limited by maximum junction temperature  $150^{\circ}$ C (initial temperature  $T_i$ =25°C).



# **Electrical Characteristics** $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

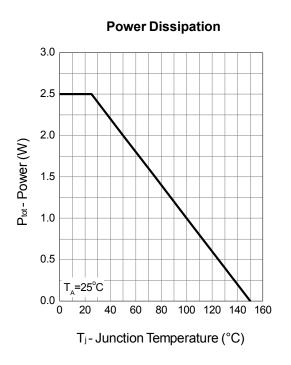
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit			
Static Characteristics									
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-30	-	-	V			
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-1				
		T <sub>J</sub> =85°C	-	-	-30	μA			
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = -250 \mu A$	-1.0	-1.5	-2.3	V			
I <sub>GSS</sub>	Gate Leakage Current	$V_{GS}$ =±25V, $V_{DS}$ =0V	-	-	±100	nA			
D C	Drain-Source On-state Resistance	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-8.9A		15	21	mO			
R <sub>DS(ON)</sub> <sup>c</sup>	Dialii-Source Oil-state Resistance	V <sub>GS</sub> =-4.5V, I <sub>DS</sub> =-5.6A	ı	22	32	mΩ			
Diode Cha	Diode Characteristics								
V <sub>SD</sub> <sup>c</sup>	Diode Forward Voltage	I <sub>SD</sub> =-1A, V <sub>GS</sub> =0V	-	-0.7	-1	V			
t <sub>rr</sub> <sup>d</sup>	Reverse Recovery Time	I <sub>SD</sub> =-8.9A,	-	18	-	ns			
Q <sub>rr</sub> <sup>d</sup>	Reverse Recovery Charge	dI <sub>SD</sub> /dt=100A/μs	-	9	-	nC			
Dynamic	Dynamic Characteristics d								
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,F=1MHz	-	3.6	-	Ω			
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V,	-	1004	-	pF			
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-15V,	-	204	-				
C <sub>rss</sub>	Reverse Transfer Capacitance	Frequency=1.0MHz	-	154	-				
t <sub>d(ON)</sub>	Turn-on Delay Time		-	8.8	-				
t <sub>r</sub>	Turn-on Rise Time	$V_{DD}$ =-15V, $R_L$ =15 $\Omega$ ,	-	10.4	-	no			
t <sub>d(OFF)</sub>	Turn-off Delay Time	$I_{DS}$ =-1A, $V_{GEN}$ =-10V, $R_{G}$ =6 $\Omega$	-	35.2	-	ns			
t <sub>f</sub>	Turn-off Fall Time		-	46.8	-				
Gate Chai	Gate Charge Characteristics d								
$Q_{g}$	Total Gate Charge	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>DS</sub> =-8.9A	-	20	-				
9	Total Gate Charge		-	10	-	_			
$Q_{gs}$	Gate-Source Charge	$V_{DS}$ =-15V, $V_{GS}$ =-4.5V,	-	3.8	-	nC			
$Q_{gd}$	Gate-Drain Charge	I <sub>DS</sub> =-8.9A	-	5.7	-				
Qgth	Threshold Gate Charge		-	1	-				

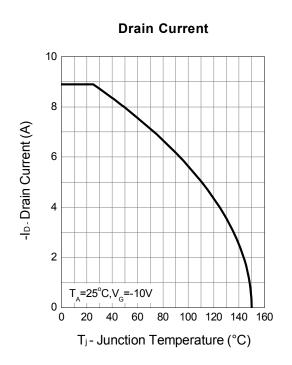
Note c : Pulse test; pulse width≤300µs, duty cycle≤2%.

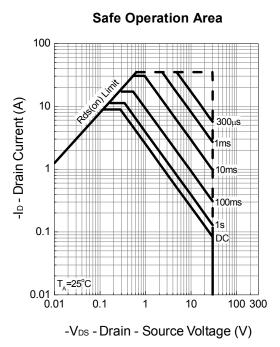
Note d: Guaranteed by design, not subject to production testing.

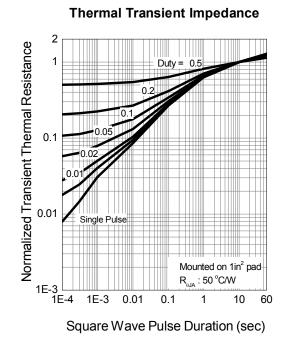


## **Typical Operating Characteristics**



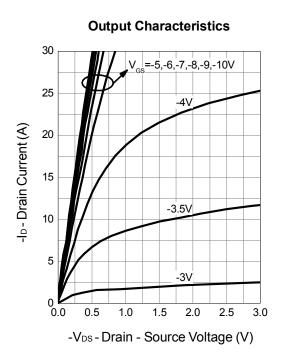


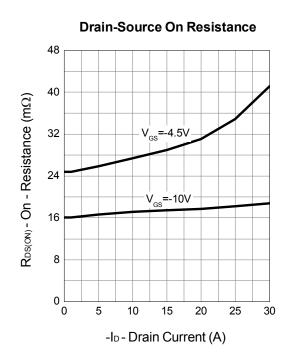


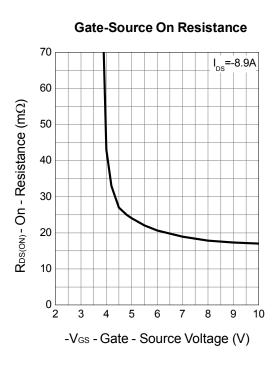


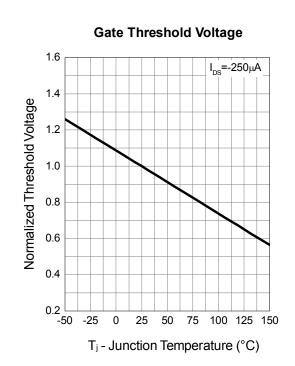


## **Typical Operating Characteristics (Cont.)**





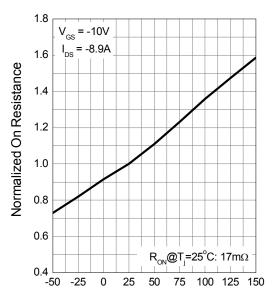






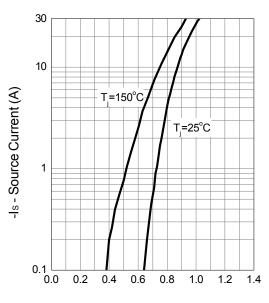
## **Typical Operating Characteristics (Cont.)**

#### **Drain-Source On Resistance**



T<sub>j</sub>- Junction Temperature (°C)

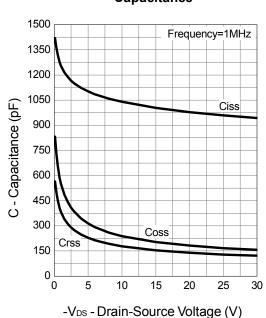
#### **Source-Drain Diode Forward**

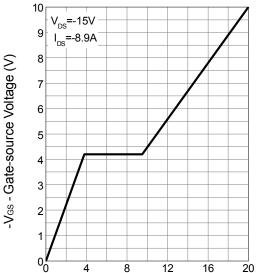


-V<sub>SD</sub> - Source-Drain Voltage (V)

**Gate Charge** 

### Capacitance

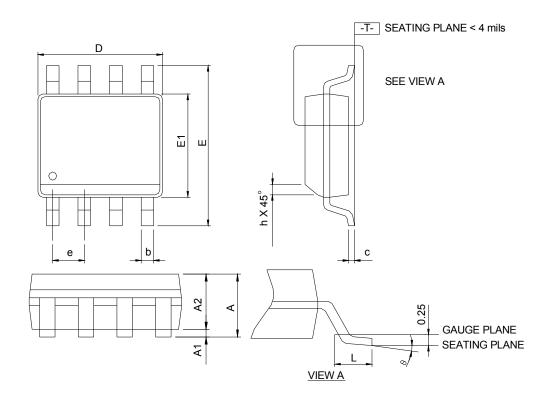




Q<sub>G</sub> - Gate Charge (nC)



## Package Information SOP-8

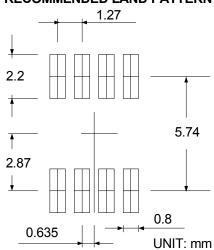


Ş	SOP-8				
\$ M P	MILLIMETERS		INCHES		
5	MIN.	MAX.	MIN.	MAX.	
Α		1.75		0.069	
A1	0.10	0.25	0.004	0.010	
A2	1.25		0.049		
b	0.31	0.51	0.012	0.020	
С	0.17	0.25	0.007	0.010	
D	4.80	5.00	0.189	0.197	
Е	5.80	6.20	0.228	0.244	
E1	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
h	0.25	0.50	0.010	0.020	
L	0.40	1.27	0.016	0.050	
θ	0°	8°	0°	8°	

Note: 1. Follow JEDEC MS-012 AA.

- Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
- 3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

#### **RECOMMENDED LAND PATTERN**





#### **Attention**

- 1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.
- 2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.
- 3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- 4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- 5,In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- 6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.
- 7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- 8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.
- 9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Winsok manufacturer:

Other Similar products are found below:

614233C 648584F FDPF9N50NZ IRFD120 IRFF430 JANTX2N5237 2N7000 FCA20N60\_F109 FDZ595PZ 2SK2267(Q) 2SK2545(Q,T)
405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C PSMN4R2-30MLD

TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7

NTE2384 NTE2969 NTE6400A DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B

IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7

BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IPS60R1K0PFD7SAKMA1 IPS60R360PFD7SAKMA1

IPS60R600PFD7SAKMA1 IPS60R210PFD7SAKMA1 DMN2990UFB-7B